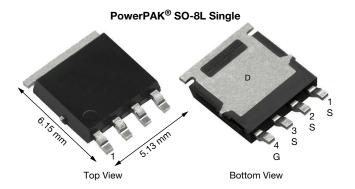
SQJA92EP

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Vishay Siliconix

Automotive N-Channel 80 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY	
V _{DS} (V)	80
$R_{DS(on)} (\Omega)$ at $V_{GS} = 10 V$	0.0095
I _D (A)	57
Configuration	Single
Package	PowerPAK SO-8L

FEATURES

- TrenchFET[®] power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>



HALOGEN

FREE

ABSOLUTE MAXIMUM RATING	S (T _C = 25 °C, unles	s otherwise noted	(k	
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V _{DS}	80	V
Gate-source voltage		V _{GS}	± 20	V
Continuous drain current	T _C = 25 °C		57	
Continuous drain current	$T_{\rm C} = 125 ^{\circ}{\rm C}$	ID	33	
Continuous source current (diode conduction	on)	I _S	60	A
Pulsed drain current ^a		I _{DM}	150	
Single pulse avalanche current	L = 0.1 mH	I _{AS}	33	
Single pulse avalanche energy	L = 0.1 IIIH	E _{AS}	54	mJ
	T _C = 25 °C	П	68	w
Maximum power dissipation ^a	T _C = 125 °C	P _D	22	~ ~~
Operating junction and storage temperature	e range	T _J , T _{stg}	-55 to +175	°C
Soldering recommendations (peak tempera	ture) ^{c, d}		260	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount ^b	R _{thJA}	68	°C/W
Junction-to-case (drain)		R _{thJC}	2.2	0/10

Notes

b. When mounted on 1" square PCB (FR4 material).

d. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

a. Pulse test; pulse width $\leq 300~\mu\text{s},$ duty cycle $\leq 2~\%.$

c. See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

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PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static		-					
Drain-source breakdown voltage	V _{DS}	V_{GS} = 0, I _D = 250 µA		80	-	-	v
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	= V _{GS} , I _D = 250 μΑ	2.5	3.0	3.5	v
Gate-source leakage	I _{GSS}	V _{DS} =	0 V, $V_{GS} = \pm 20 V$	-	-	± 100	nA
Zero gate voltage drain current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = 80 V	-	-	1	μA
		$V_{GS} = 0 V$	$V_{DS} = 80 \text{ V}, \text{ T}_{J} = 125 ^{\circ}\text{C}$	-	-	50	
		$V_{GS} = 0 V$	V _{DS} = 80 V, T _J = 175 °C	-	-	150	
On-state drain current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	30	-	-	Α
	_ ()	$V_{GS} = 10 V$	I _D = 10 A	-	0.0078	0.0095	
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 10 A, T _J = 125 °C	-	-	0.0152	Ω
		V _{GS} = 10 V	I _D = 10 A, T _J = 175 °C	-	-	0.0188	1
Forward transconductance b	g fs	V _{DS}	= 15 V, I _D = 10 A	-	36	-	S
Dynamic ^b				I	I		1
Input capacitance	C _{iss}			-	2005	2650	
Output capacitance	Coss	$V_{GS} = 0 V$	V _{DS} = 25 V, f = 1 MHz	-	1055	1400	pF
Reverse transfer capacitance	C _{rss}	1		-	36	50	
Total gate charge ^c	Qg			-	30	45	
Gate-source charge ^c	Q _{gs}	V _{GS} = 10 V	$V_{DS} = 40 \text{ V}, \text{ I}_{D} = 5 \text{ A}$	-	9	-	nC
Gate-drain charge ^c	Q _{gd}	1		-	5	-	
Gate resistance	R _q	f = 1 MHz		0.20	0.45	0.68	Ω
Turn-on delay time ^c	t _{d(on)}			_	15	25	
Rise time ^c	t _r	Vpp	- V _{DD} = 40 V, R _L = 8 Ω		5	10	- ns
Turn-off delay time ^c	t _{d(off)}	$I_D \cong 5 \text{ A}, V_{\text{GEN}} = 10 \text{ V}, \text{ R}_g = 1 \Omega$		-	24	40	
Fall time ^c	t _f			_	14	25	
Source-Drain Diode Ratings and Charac	cteristics ^b					1	1
Pulsed current ^a	I _{SM}			-	-	150	Α
Forward voltage	V _{SD}	$I_{\rm F} = 10$ A, $V_{\rm GS} = 0$		_	0.8	1.2	V
Body diode reverse recovery time	t _{rr}	1		-	57	115	ns
Body diode reverse recovery charge	Q _{rr}	10	$A = \frac{100}{100}$	-	88	180	nC
Reverse recovery fall time	t _a	IF = 10	A, di/dt = 100 A/µs	-	27	-	ns
Reverse recovery rise time	t _b			-	31	-	115
Body diode peak reverse recovery current	I _{RM(REC)}			-	-2.9	-6	Α

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

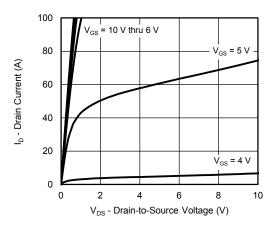
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

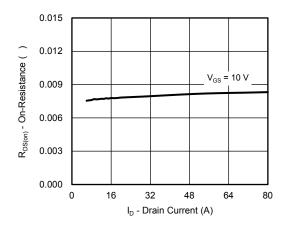
2



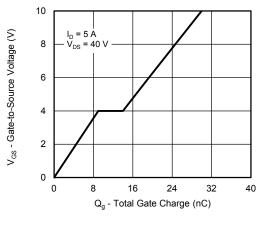
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



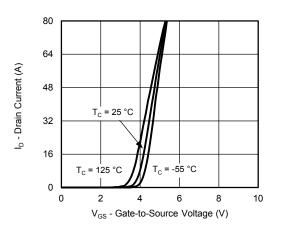
Output Characteristics



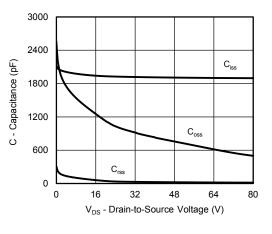
On-Resistance vs. Drain Current



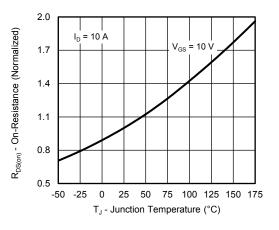
Gate Charge



Transfer Characteristics



Capacitance



On-Resistance vs. Junction Temperature

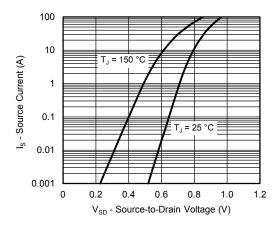
S16-2322-Rev. A, 14-Nov-16

3 stions, contact: automostechsupp Document Number: 75095

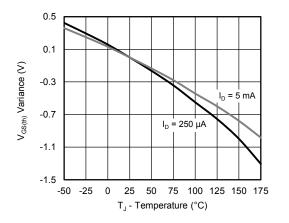
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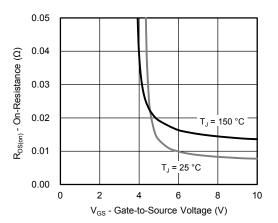
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



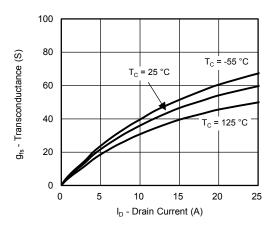
Source Drain Diode Forward Voltage



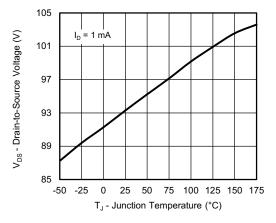
Threshold Voltage



On-Resistance vs. Gate-to Source Voltage



Transconductance



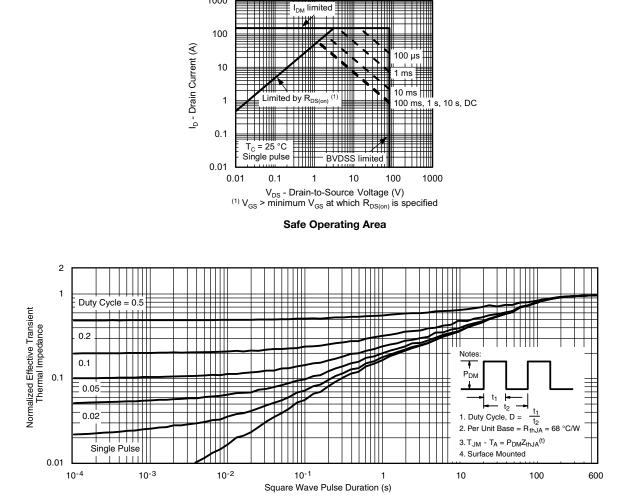
Drain Source Breakdown vs. Junction Temperature

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TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)

1000



Normalized Thermal Transient Impedance, Junction-to-Ambient

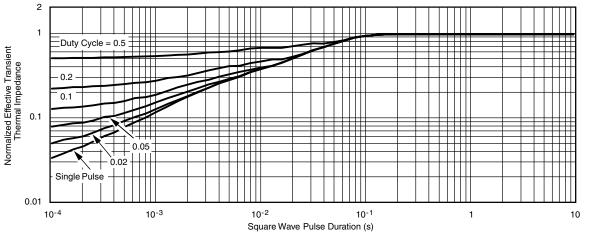


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Document Number: 75095

TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

• The characteristics shown in the two graphs

S16-2322-Rev. A, 14-Nov-16

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?75095.

6









Package Information



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		MILLIMETERS		INCHES			
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
А	1.00	1.07	1.14	0.039	0.042	0.045	
A1	0.00	-	0.127	0.00	-	0.005	
b	0.33	0.41	0.48	0.013	0.016	0.019	
b1	0.44	0.51	0.58	0.017	0.020	0.023	
b2	4.80	4.90	5.00	0.189	0.193	0.197	
b3		0.094			0.004		
b4		0.47			0.019		
С	0.20	0.25	0.30	0.008	0.010	0.012	
D	5.00	5.13	5.25	0.197	0.202	0.207	
D1	4.80	4.90	5.00	0.189	0.193	0.197	
D2	3.86	3.96	4.06	0.152	0.156	0.160	
D3	1.63	1.73	1.83	0.064	0.068	0.072	
е		1.27 BSC		0.050 BSC			
E	6.05	6.15	6.25	0.238	0.242	0.246	
E1	4.27	4.37	4.47	0.168	0.172	0.176	
E2	2.75	2.85	2.95	0.108	0.112	0.116	
E3	6.05	6.22	6.40	0.238	0.245	0.252	
F	-	-	0.15	-	-	0.006	
L	0.62	0.72	0.82	0.024	0.028	0.032	
L1	0.92	1.07	1.22	0.036	0.042	0.048	
К		0.51		0.020			
W		0.23		0.009			
W1	0.41		0.016				
W2	2.82		0.111				
W3		2.96		0.117			
θ	0°	-	10°	0°	-	10°	

Note

• Millimeters will govern



RECOMMENDED MINIMUM PAD FOR PowerPAK[®] SO-8L SINGLE



Recommended Minimum Pads Dimensions in mm (inches)

Revision: 07-Feb-12



Vishay

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1